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WEST[Generate Collection](#)[Print](#)**Search Results - Record(s) 1 through 2 of 2 returned.**☐ 1. Document ID: KR 2003047571 A

L1: Entry 1 of 2

File: DWPI

Jun 18, 2003

DERWENT-ACC-NO: 2003-728774

DERWENT-WEEK: 200369

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TITLE: Formation method of silicon thin film

Basic Abstract Text (2):

DETAILED DESCRIPTION - The method comprises the steps of forming an intermediate crystal layer(12) as a seed layer on a substrate(12), which is made of a material having a lattice constant similar to that of silicon; forming a silicon layer(14) on the intermediate crystal layer; and heating the silicon layer(14). Preferably the crystal layer(12) is made of CeO₂, CaF₂ or ZnS, and is evaporation deposited at a temperature of 500 deg.C or less. Preferably the substrate is made of glass, plastic, a metal or a metal alloy, and it comprises further a buffer layer on the surface. The silicon layer is formed at a temperature of 25-500 deg.C and is an amorphous layer.

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	Claims	KWC	Draw Desc	Image
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☐ 2. Document ID: EP 432038 A DE 69026910 E FR 2655463 A JP 03266241 A US 5169504 A EP 432038 B1

L1: Entry 2 of 2

File: DWPI

Jun 12, 1991

DERWENT-ACC-NO: 1991-173273

DERWENT-WEEK: 199629

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TITLE: Magneto-optical material uses crystalline oxide layer - on support with reflective and thermal barrier layers to prevent damage during recrystallisation of amorphous oxide(s)

Equivalent Abstract Text (1):

Method for preparing a magneto-optic memory comprising on a support (22) not resisting high temperatures, such as a glass, metal or plastic support, a sensitive plain film (21) of a magneto-optic material intended to receive at each point the recording of one of the two binary digits 0 and 1 in the form of small domains juxtaposed and magnetized perpendicular to the plane of the film in one of two possible directions with respect to the latter, at least one reflecting film (28) and/or one film (30) constituting a thermic screen is placed between the support (22) and the sensitive film (21), the sensitive film (21) being constituted by the cathodic evaporation depositing or by other means of a magnetic oxide selected from hexaferrites and ferrimagnetic garnets, the preceding deposit being followed by a crystallization of the amorphous section with the aid of a fast annealing, lasting a few seconds at a temperature of between 600 deg.C and 650 deg.C.

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	Claims	KWIC	Draw Desc	Image
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Terms	Documents
(evaporation adj deposit\$) same amorphous same metal	2

Display Format:[KWIC](#)[Change Format](#)[Previous Page](#)[Next Page](#)

WEST[Generate Collection](#)[Print](#)**Search Results - Record(s) 1 through 17 of 17 returned.**☐ 1. Document ID: US 6610428 B2

L2: Entry 1 of 17

File: USPT

Aug 26, 2003

US-PAT-NO: 6610428

DOCUMENT-IDENTIFIER: US 6610428 B2

TITLE: Controlled conversion of metal oxyfluorides into superconducting oxides

DATE-ISSUED: August 26, 2003

INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Smith; John A.	Nashua	NH		
Cima; Michael I.	Winchester	MA		
Sonnenberg; Neville	Newton	MA		

US-CL-CURRENT: [428/701](#); [428/930](#), [505/237](#), [505/238](#)[Full](#) | [Title](#) | [Citation](#) | [Front](#) | [Review](#) | [Classification](#) | [Date](#) | [Reference](#) | [Sequences](#) | [Attachments](#)[KIMC](#) | [Draw Desc](#) | [Image](#)☐ 2. Document ID: US 6534784 B2

L2: Entry 2 of 17

File: USPT

Mar 18, 2003

US-PAT-NO: 6534784

DOCUMENT-IDENTIFIER: US 6534784 B2

TITLE: Metal-oxide electron tunneling device for solar energy conversion

DATE-ISSUED: March 18, 2003

INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Eliasson; Blake J.	Boulder	CO		
Model; Garret	Boulder	CO		

US-CL-CURRENT: [257/25](#); [136/206](#), [136/255](#), [257/17](#), [257/21](#)[Full](#) | [Title](#) | [Citation](#) | [Front](#) | [Review](#) | [Classification](#) | [Date](#) | [Reference](#) | [Sequences](#) | [Attachments](#)[KIMC](#) | [Draw Desc](#) | [Image](#)☐ 3. Document ID: US 6297539 B1

L2: Entry 3 of 17

File: USPT

Oct 2, 2001

US-PAT-NO: 6297539

DOCUMENT-IDENTIFIER: US 6297539 B1

TITLE: Doped zirconia, or zirconia-like, dielectric film transistor structure and deposition method for same

DATE-ISSUED: October 2, 2001

INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Ma; Yanjun	Vancouver	WA		
Ono; Yoshi	Camas	WA		

US-CL-CURRENT: 257/410; 257/411, 257/E21.193, 257/E21.274, 257/E29.162, 257/E29.165, 438/591, 438/785

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments
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KIMC	Draw Desc	Image
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☐ 4. Document ID: US 6207589 B1

L2: Entry 4 of 17

File: USPT

Mar 27, 2001

US-PAT-NO: 6207589

DOCUMENT-IDENTIFIER: US 6207589 B1

TITLE: Method of forming a doped metal oxide dielectric film

DATE-ISSUED: March 27, 2001

INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Ma; Yanjun	Vancouver	WA		
Ono; Yoshi	Camas	WA		

US-CL-CURRENT: 438/785; 257/E21.193, 257/E29.162, 257/E29.165, 438/778, 438/783, 438/784

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments
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KIMC	Draw Desc	Image
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☐ 5. Document ID: US 6172009 B1

L2: Entry 5 of 17

File: USPT

Jan 9, 2001

US-PAT-NO: 6172009

DOCUMENT-IDENTIFIER: US 6172009 B1

TITLE: Controlled conversion of metal oxyfluorides into superconducting oxides

DATE-ISSUED: January 9, 2001

INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Smith; John A.	Nashua	NH		
Cima; Michael J.	Winchester	MA		
Sonnenberg; Neville	Newton	MA		

US-CL-CURRENT: 505/473; 505/446, 505/447, 505/474, 505/475, 505/477, 505/500, 505/742

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments
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KWIC	Draw Desc	Image
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☐ 6. Document ID: US 6060755 A

L2: Entry 6 of 17

File: USPT

May 9, 2000

US-PAT-NO: 6060755

DOCUMENT-IDENTIFIER: US 6060755 A

TITLE: Aluminum-doped zirconium dielectric film transistor structure and deposition method for same

DATE-ISSUED: May 9, 2000

INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Ma; Yanjun	Vancouver	WA		
Ono; Yoshi	Camas	WA		

US-CL-CURRENT: 257/410; 257/406, 257/411, 257/E21.193, 257/E29.162, 257/E29.165

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments
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KWIC	Draw Desc	Image
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☐ 7. Document ID: US 5435903 A

L2: Entry 7 of 17

File: USPT

Jul 25, 1995

US-PAT-NO: 5435903

DOCUMENT-IDENTIFIER: US 5435903 A

TITLE: Process for the electrodeposition of an amorphous cobalt-iron-phosphorus alloy

DATE-ISSUED: July 25, 1995

INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Oda; Masaharu	Hiroshima			JP
Ohashi; Hidehiko	Hiroshima			JP
Kamada; Kensuke	Hiroshima			JP

US-CL-CURRENT: 205/77; 205/258

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments
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KWIC	Draw Desc	Image
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☐ 8. Document ID: US 5399502 A

L2: Entry 8 of 17

File: USPT

Mar 21, 1995

US-PAT-NO: 5399502

DOCUMENT-IDENTIFIER: US 5399502 A

TITLE: Method of manufacturing of electroluminescent devices

DATE-ISSUED: March 21, 1995

INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Friend; Richard H.	Cambridge			GB
Burroughes; Jeremy H.	New York	NY		
Bradley; Donal D.	Cambridge			GB

US-CL-CURRENT: 438/22; 257/E51.018, 257/E51.029, 257/E51.031, 438/99

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments
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KMC	Draw Desc	Image
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☐ 9. Document ID: US 5342719 A

L2: Entry 9 of 17

File: USPT

Aug 30, 1994

US-PAT-NO: 5342719

DOCUMENT-IDENTIFIER: US 5342719 A

TITLE: Imaging members having a hydroxy aryl amine charge transport layer

DATE-ISSUED: August 30, 1994

INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Pai; Damodar M.	Fairport	NY		
Yanus; John F.	Webster	NY		
DeFeo; Paul J.	Sodus Point	NY		
Toth; Alan E. J.	Burlington			CA
Mychajlowski; Walter	Georgetown			CA
Popovic; Zoran	Mississauga			CA

US-CL-CURRENT: 430/58.8; 430/73

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments
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KMC	Draw Desc	Image
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☐ 10. Document ID: US 5306586 A

L2: Entry 10 of 17

File: USPT

Apr 26, 1994

US-PAT-NO: 5306586

DOCUMENT-IDENTIFIER: US 5306586 A

**** See image for Certificate of Correction ****

TITLE: Dual layer switch photoreceptor structures for digital imaging

DATE-ISSUED: April 26, 1994

INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Pai; Damodar M.	Fairport	NY		
Melnyk; Andrew R.	Rochester	NY		
Stolka; Milan	Fairport	NY		

US-CL-CURRENT: 430/58.5; 430/58.1, 430/58.65, 430/78, 430/79, 430/87, 430/88, 430/91,

430/94

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments
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KIMC	Draw Desc	Image
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☐ 11. Document ID: US 5289455 A

L2: Entry 11 of 17

File: USPT

Feb 22, 1994

US-PAT-NO: 5289455

DOCUMENT-IDENTIFIER: US 5289455 A

**** See image for Certificate of Correction ****

TITLE: Information recording and/or reproducing apparatus

DATE-ISSUED: February 22, 1994

INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Kuroda; Ryo	Atsugi			JP
Yamano; Akihiko	Yokohama			JP
Nose; Hiroyasu	Zama			JP
Miyazaki; Toshihiko	Hiratsuka			JP
Oguchi; Takahiro	Atsugi			JP

US-CL-CURRENT: 369/126; 250/306

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments
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KIMC	Draw Desc	Image
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☐ 12. Document ID: US 5247190 A

L2: Entry 12 of 17

File: USPT

Sep 21, 1993

US-PAT-NO: 5247190

DOCUMENT-IDENTIFIER: US 5247190 A

TITLE: Electroluminescent devices

DATE-ISSUED: September 21, 1993

INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Friend; Richard H.	Cambridge			GB
Burroughes; Jeremy H.	New York	NY		
Bradley; Donal D.	Cambridge			GB

US-CL-CURRENT: 257/40; 257/103, 257/E51.029, 257/E51.031, 313/504

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments
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KIMC	Draw Desc	Image
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☐ 13. Document ID: US 5040166 A

L2: Entry 13 of 17

File: USPT

Aug 13, 1991

US-PAT-NO: 5040166

DOCUMENT-IDENTIFIER: US 5040166 A

TITLE: Magneto-optical recording medium having a reflective film of Ag and Mn or Ag, Mn and Sn

DATE-ISSUED: August 13, 1991

INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Kobayashi; Masanobu	Tokyo			JP
Maeno; Yoshinori	Tokyo			JP
Oishi; Kayoko	Tokyo			JP

US-CL-CURRENT: 369/275.2; 360/131, 369/13.35, 369/288, 428/694ML, 428/694RL

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments
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KIMC	Draw Desc	Image
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☐ 14. Document ID: US 5009762 A

L2: Entry 14 of 17

File: USPT

Apr 23, 1991

US-PAT-NO: 5009762

DOCUMENT-IDENTIFIER: US 5009762 A

**** See image for Certificate of Correction ****

TITLE: Magneto-optical recording medium having protective film with increased kerr effect and improved protection characteristic and manufacturing method of the same

DATE-ISSUED: April 23, 1991

INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Maeno; Yoshinori	Tokyo			JP
Kobayashi; Masanobu	Tokyo			JP
Oishi; Kayoko	Tokyo			JP

US-CL-CURRENT: 204/192.16; 204/192.2

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments
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KIMC	Draw Desc	Image
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☐ 15. Document ID: US 4950547 A

L2: Entry 15 of 17

File: USPT

Aug 21, 1990

US-PAT-NO: 4950547

DOCUMENT-IDENTIFIER: US 4950547 A

TITLE: Magneto-optical recording medium having protective film with increased Kerr effect and improved protection characteristic and manufacturing method of the same

DATE-ISSUED: August 21, 1990

INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Maeno; Yoshinori	Tokyo			JP
Kobayashi; Masanobu	Tokyo			JP
Oishi; Kayoko	Tokyo			JP

US-CL-CURRENT: 428/471; 428/694DE, 428/694ML, 428/694MT, 428/694NF, 428/694XS,
428/697, 428/702

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments
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KWIC	Draw Desc	Image
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☐ 16. Document ID: US 4422063 A

L2: Entry 16 of 17

File: USPT

Dec 20, 1983

US-PAT-NO: 4422063

DOCUMENT-IDENTIFIER: US 4422063 A

TITLE: Semiconductor strain gauge

DATE-ISSUED: December 20, 1983

INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Pryor; Roger W.	Trumbull	CT		

US-CL-CURRENT: 338/2; 257/417, 257/53

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments
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KWIC	Draw Desc	Image
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☐ 17. Document ID: US 4410870 A

L2: Entry 17 of 17

File: USPT

Oct 18, 1983

US-PAT-NO: 4410870

DOCUMENT-IDENTIFIER: US 4410870 A

TITLE: Semiconductor strain gauge

DATE-ISSUED: October 18, 1983

INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Pryor; Roger W.	Trumbull	CT		

US-CL-CURRENT: 338/2; 257/53

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments
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KWIC	Draw Desc	Image
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(evaporation adj deposit\$) same amorphous same metal

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